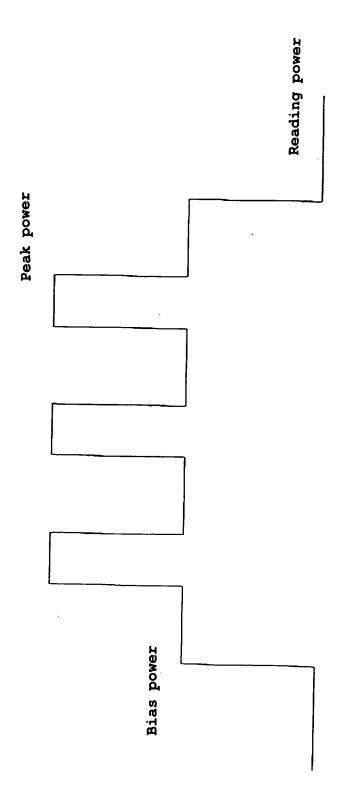


OBLON, SPIVAK, ET AL DOCKET #: 218233US2 INV: Toshio INASE, et al. SHEET _1_ OF_5_



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FIG. 2

| 25 |
|----|
| 24 |
| 23 |
| 22 |
| 21 |

21: Substrate

22: Protective layer

23: Recording layer

24: Protective layer

25: Reflective layer

FIG. 3

| 36 |
|------|
| 35 |
| 34 |
| 33 |
| 32 |
| .3.1 |

31: Substrate

32: Protective layer

33: Recording layer

34: Protective layer

35: Reflective layer

36: Protective coating layer

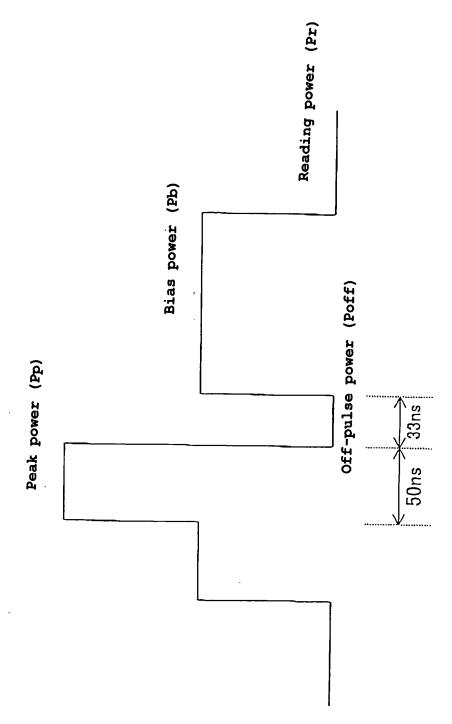


FIG.

Comparative Example 3 SiC content -0-10 mol8 -G-50 mol8 -- 70 mol8 -4-30 mol% -m-0 mol8 ___ 1 mol8 7.0×10^{-7} 12 Linear velocity (m/s) 1.5×10 2.0×10^{-7} 9 35 30 25 20 15 9 Erasability (dB)

FIG. 5

OBLON, SPIVAK, ET AL DOCKET #: 218233US2 INV: Toshio INASE, et al. SHEET _5_ OF_5_

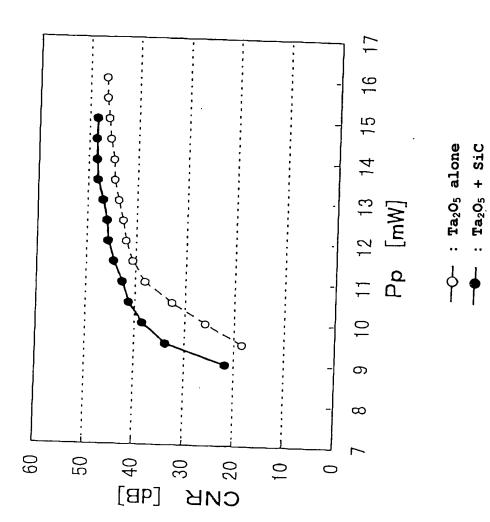


FIG.